

STPS1545C-Y

Automotive power Schottky rectifier

Features

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Avalanche capability specified
- AEC-Q101 qualified

Description

Dual center tap Schottky rectifier suited for high frequency DC to DC converters.

Packaged in D²PAK, this device is especially intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

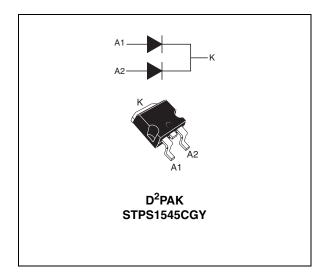


Table 1. Device summary

I _{F(AV)}	2 x 7.5 A
V _{RRM}	45 V
T _{j (max)}	175 °C
V _{F(max)}	0.57 V

1 Characteristics

Parameter	Value	Unit		
Repetitive peak reverse voltage			45	
RMS forward voltage			20	А
Average forward current $\delta = 0.5$	T _c = 157 °C	Per diode	7.5	А
Surge non repetitive forward current	t _p = 10 ms Sinusoidal		150	А
Peak repetitive reverse current	t _p = 2 μs square F = 1 kHz		1	А
Non repetitive peak reverse current $t_p = 100 \ \mu s \ square$			2	А
Repetitive peak avalanche power $t_p = 1 \ \mu s \ T_j = 25 \ ^{\circ}C$			25 °C 2700	
Storage temperature range	-65 to +175	°C		
Maximum operating junction temperature ⁽¹⁾			-40 to +175	°C
Critical rate of rise of reverse voltage			10000	
	Repetitive peak reverse voltage RMS forward voltage Average forward current $\delta = 0.5$ Surge non repetitive forward current Peak repetitive reverse current Non repetitive peak reverse current Repetitive peak avalanche power Storage temperature range Maximum operating junction temperature	Repetitive peak reverse voltageRMS forward voltageAverage forward current $\delta = 0.5$ $T_c = 157 ^{\circ}C$ Surge non repetitive forward current $t_p = 10 \text{ms}$ SinusoidalPeak repetitive reverse current $t_p = 2 \mu s squareNon repetitive peak reverse currentt_p = 1 \mu s T_j = 100 \mu s sRepetitive peak avalanche powert_p = 1 \mu s T_j = 100 \mu s sStorage temperature rangeMaximum operating junction temperature ^{(1)}$	Repetitive peak reverse voltageRMS forward voltageAverage forward current $\delta = 0.5$ $T_c = 157 \ ^{\circ}C$ Per diodeSurge non repetitive forward current $t_p = 10 \ \text{ms}$ SinusoidalSinusoidalPeak repetitive reverse current $t_p = 2 \ \mu s \ square$ $F = 1 \ kHz$ Non repetitive peak reverse current $t_p = 100 \ \mu s \ square$ $F = 100 \ \mu s \ square$ Repetitive peak avalanche power $t_p = 1 \ \mu s \ T_j = 25 \ ^{\circ}C$ Storage temperature rangeMaximum operating junction temperature (1)	Repetitive peak reverse voltage45RMS forward voltage20Average forward current $\delta = 0.5$ $T_c = 157 ^{\circ}C$ Per diode7.5Surge non repetitive forward current $t_p = 10 \text{ms}$ Sinusoidal150150Peak repetitive reverse current $t_p = 2 \mu s \text{square}$ $F = 1 \text{kHz}$ 1Non repetitive peak reverse current $t_p = 100 \mu s \text{square}$ $I_p = 100 \mu s \text{square}$ 2Repetitive peak avalanche power $t_p = 1 \mu s T_j = 25 ^{\circ}C$ 2700Storage temperature range-65 to +175-40 to +175Maximum operating junction temperature $^{(1)}$ -40 to +175

Table 2. Absolute Ratings (limiting values)

1. $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3.Thermal resistances

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case	Per diode Total	3.0 1.7	°C/W
R _{th(c)}	Coupling		0.35	

When the diodes 1 and 2 are used simultaneously : Δ Tj(diode 1) = P(diode1) x R_{th(j-c)}(Per diode) + P(diode 2) x R_{th(c)}

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _V	-	-	100	μA
IR Preverse leakage current	T _j = 125 °C	V _R =V _{RRM}	-	5	15	mA	
V _F ⁽¹⁾ Forward voltage drop	T _j = 125 °C	I _F = 7.5A	-	0.5	0.57		
	Forward voltage drop	T _j = 25 °C	I _F = 15 A	-	-	0.84	V
		T _j = 125 °C	I _F = 15 A	-	0.65	0.72	

1. Pulse test: tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation: $P = 0.42 \text{ x } I_{F(AV)} + 0.020 \text{ } I_{F}^{2}(\text{RMS})$



Average forward current versus

ambient temperature

Figure 1. Average forward power dissipation Figure 2. versus average forward current (per diode)

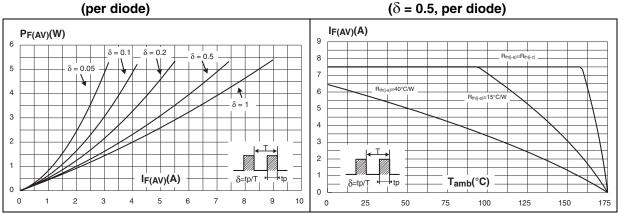
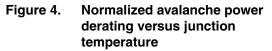
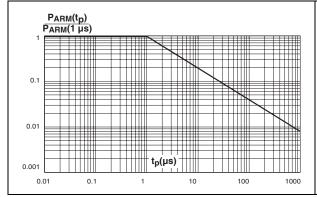


Figure 3. Normalized avalanche power derating versus pulse duration





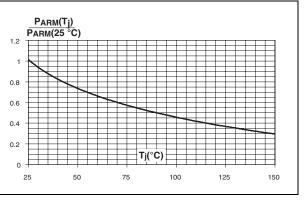


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

57

Figure 6. Relative variation of thermal impedance junction to case versus pulse duration

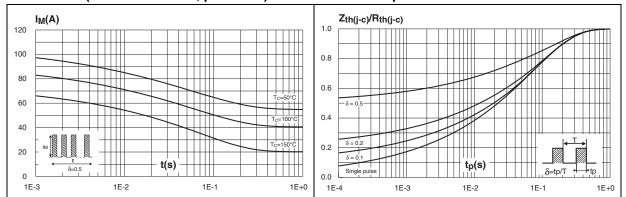


Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)

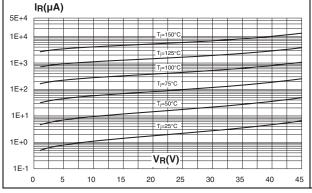


Figure 8. Junction capacitance versus reverse voltage applied (typical values, per diode)

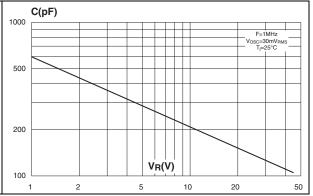
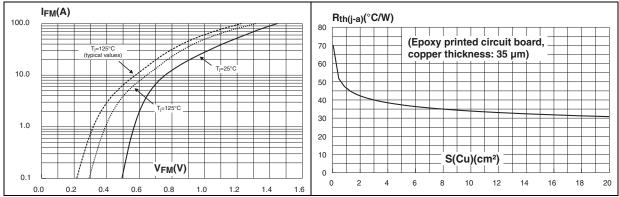


Figure 9. Forward voltage drop versus forward current (maximum values, per diode)

Figure 10. Thermal resistance junction to ambient versus copper surface under tab





2 Package Information

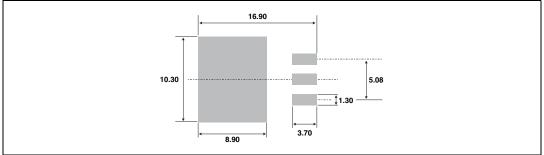
- Epoxy meets UL94, V0
- Lead-free package

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Figure 11. D²PAK dimensions

			Dimensions			
		Ref	Millimeters		Inches	
i			Min.	Max.	Min.	Max.
		А	4.40	4.60	0.173	0.181
	C2 → – (←	A1	2.49	2.69	0.098	0.106
		A2	0.03	0.23	0.001	0.009
	D	В	0.70	0.93	0.027	0.037
L	A1	B2	1.14	1.70	0.045	0.067
		С	0.45	0.60	0.017	0.024
		C2	1.23	1.36	0.048	0.054
	D	8.95	9.35	0.352	0.368	
G		Е	10.00	10.40	0.393	0.409
		G	4.88	5.28	0.192	0.208
		L	15.00	15.85	0.590	0.624
	M * V2	L2	1.27	1.40	0.050	0.055
	* FLAT ZONE NO LESS THAN 2mm	L3	1.40	1.75	0.055	0.069
		М	2.40	3.20	0.094	0.126
		R	0.40	typ.	0.016	6 typ.
		V2	0°	8°	0°	8°







3 Ordering information

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS1545CGY-TR	STPS1545CGY	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 6.Document revision history

Date	Revision	Changes
23-May-2011	1	Initial release.



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